

SILICON DIODE CHIP

This SILICON DIODE CHIP is a Si-based Diode. It has electrical characteristics like lower leakage current, high electrostatic discharge ability and other advantages , it also has extra small size.

● Features

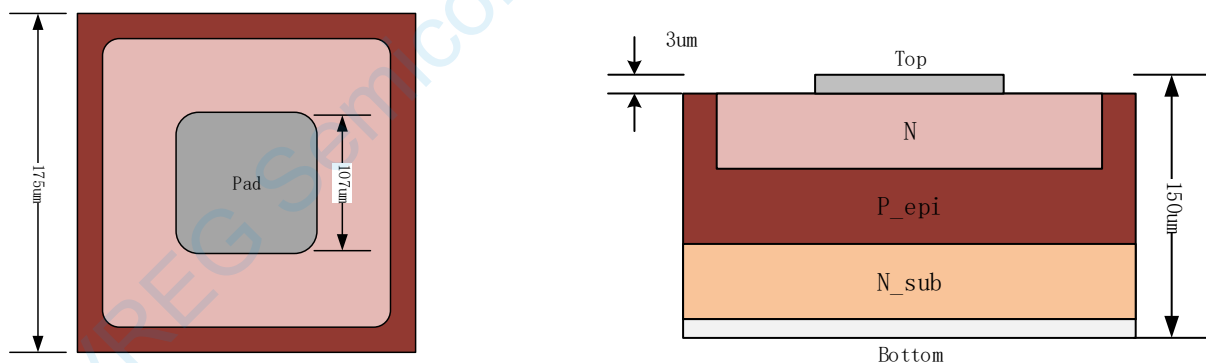
- ▶ Si-based NPN type
- ▶ Ultra-small size 6.9mil * 6.9mil

● Structure

- ▶ Electrode topside: AlCu
- ▶ Electrode backside: Ag

● Size

Parameter	Value (mil)	Value (mm)
Chip size	6.9mil x 6.9mil (±0.4mil)	0.175mm x 0.175mm (±0.01mm)
Chip Thickness	6mil ± 0.4mil	0.150mm ± 0.010mm
Top Metal Thickness	0.118mil	0.003mm
Pad Size	4.2mil ± 0.2mil	0.107mm ± 0.005mm



● Electrical Characteristics(T= 25℃)

Parameter	Symbol	Test condition	Value	Unit
Junction temperature	T _j		150	℃
Storage temperature	T _{stg}		-55~150	℃

Electrical Characteristics(T= 25℃)

Parameter	Symbol	Min	Type	Max	Unit	Test Conditions
Forward Voltage	V_F	6	-	8	V	$I_F = 1\text{mA}$
Forward Voltage	V_F	6	-	8	V	$I_F = 10\text{mA}$
Forward Leakage Current	I_F	-	-	50	nA	$V_F = 5\text{V}$
Reverse Voltage	V_R	6	-	8	V	$I_R = 1\text{mA}$
Reverse Voltage	V_R	6	-	8	V	$I_R = 10\text{mA}$
Reverse Leakage Current	I_R	-	-	50	nA	$V_R = 5\text{V}$
ESD	-	± 30	-	-	kV	IEC 61000-4-2 (AIR)
ESD	-	± 30	-	-	kV	IEC 61000-4-2 (CONTACT)

Schematic and PIN configuration

